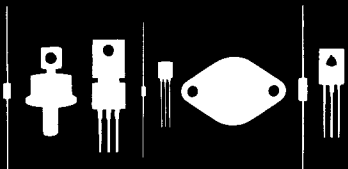


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145 Adams Avenue
Hauppauge, New York 11788



2N5262

SILICON NPN TRANSISTOR

JEDEC TO-39 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N5262 is an NPN silicon core driver transistor manufactured by the epitaxial planar process designed for high current and high speed switching applications.

MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

	SYMBOL		UNIT
Collector-Base Voltage	V_{CB0}	75	V
Collector-Emitter Voltage	V_{CE0}	50	V
Emitter-Base Voltage	V_{EB0}	5.0	V
Collector Current	I_C	2.0	A
Collector Current (PEAK)	I_{CM}	3.0	A
Power Dissipation ($T_A=25^{\circ}\text{C}$)	P_D	1.0	W
Power Dissipation	P_D	5.0	W
Operating and Storage Junction Temperature	T_J, T_{STG}	-65 TO +200	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	1.75	$^{\circ}\text{C/W}$
Thermal Resistance	θ_{JC}	0.35	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_{CES}	$V_{CE}=30\text{V}$		1.0	μA
I_{CES}	$V_{CE}=30\text{V}, T_A=100^{\circ}\text{C}$		100	μA
I_{CES}	$V_{CE}=60\text{V}$		10	μA
BV_{CB0}	$I_C=0.1\text{mA}$	75		V
BV_{CE0}	$I_C=10\text{mA}$	50		V
BV_{EB0}	$I_E=0.1\text{mA}$	5.0		V
$V_{CE(SAT)}$	$I_C=1000\text{mA}, I_B=100\text{mA}$		0.8	V
$V_{BE(SAT)}$	$I_C=1000\text{mA}, I_B=100\text{mA}$		1.4	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	35		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=500\text{mA}$	40		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=1000\text{mA}$	25		
f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	250		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		12	pF
t_{ON}	$I_C=1000\text{mA}, I_{B1}=100\text{mA}$		30	ns
t_{OFF}	$I_C=1000\text{mA}, I_{B1}=100\text{mA}, I_{B2}=100\text{mA}$		60	ns

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